

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	37167	(storage adj capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:47
L2	1911	(storage adj capacitor) same (semiconductor near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:47
L3	812	(storage adj capacitor) same (semiconductor near layer) same (gate adj (insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:47
L4	1160	(storage adj capacitor) same ((active or silicon or semiconductor) near layer) same (gate adj (insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:48
L5	96	(storage adj capacitor) same ((active or silicon or semiconductor) near layer) same (gate adj (insulating or dielectric)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:49
L6	42	(storage adj capacitor) with ((active or silicon or semiconductor) near layer) with (gate adj (insulating or dielectric)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:49
L7	369	(storage adj capacitor) same ((active or silicon or semiconductor) near layer) same (gate adj (insulating or dielectric)) same channel same (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:50
L8	76	(storage adj capacitor) same ((active or silicon or semiconductor) near layer) same (gate adj (insulating or dielectric)) same channel same (gate adj electrode) same ((first or second or upper or lower) near2 (conductive or conducting or metal or wiring or wire))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:51

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L9	7	(storage adj capacitor) same ((active or silicon or semiconductor) near layer) same (gate adj (insulating or dielectric)) same channel same (gate adj electrode) same ((first or second or upper or lower) near2 (conductive or conducting or metal or wiring or wire)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:57
L10	0	(storage adj capacitor) near2 comprising same ((active or silicon or semiconductor) near layer) same (gate adj (insulating or dielectric)) same channel same (gate adj electrode) same ((first or second or upper or lower) near2 (conductive or conducting or metal or wiring or wire)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:58
L11	0	(storage adj capacitor) near2 comprising same ((active or silicon or semiconductor) near layer) same (gate adj (insulating or dielectric)) same channel same (gate adj electrode) same ((first or second or upper or lower) near2 (conductive or conducting or metal or wiring or wire))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:58
L12	2	"09544801"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:58
L13	10	"09/544801"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:59
L14	8	l13 and (storage adj capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 12:59
L15	2	l13 and (storage adj capacitor). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:01

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L16	29	yamazaki and ((storage adj capacitor) near comprising).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:02
L17	1	yamazaki and (((storage adj capacitor) adj comprising) near10 (conductive or conducting or material)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:06
L18	3	yamazaki and (((storage adj capacitor) adj comprising) near10 (conductive or conducting or material))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:06
L19	84	yamazaki and (((storage adj capacitor)) near10 ((first or second or upper or lower or top or bottom) near2 (conductive or conducting or material)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:17
L20	42	l19 and ((storage adj capacitor) near10 (semiconductor adj layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:18
L21	23	l19 and ((storage adj capacitor) near10 (semiconductor adj layer) near10 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:19
L22	6	l19 and ((storage adj capacitor) near10 (semiconductor adj layer) near10 gate near10 (part or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:20
L23	1	l19 and ((storage adj capacitor) near10 (semiconductor adj layer) near10 (gate near2 (insulating or dielectric or oxide)) near10 (part or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:20
L24	2	l19 and ((storage adj capacitor) with (semiconductor adj layer) near10 (gate near2 (insulating or dielectric or oxide)) near10 (part or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:20
L25	3	l19 and ((storage adj capacitor) with (semiconductor adj layer) with (gate near2 (insulating or dielectric or oxide)) near10 (part or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:20

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L26	5	I19 and ((storage adj capacitor) with (semiconductor adj layer) with (gate near2 (insulating or dielectric or oxide)) with (part or portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:21
L27	32	I19 and ((storage adj capacitor) with (semiconductor adj layer) with (gate near2 (insulating or dielectric or oxide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:22
L28	40	I19 and ((storage adj capacitor) with ((active or semiconductor) adj (film or layer)) with (gate near2 (insulating or dielectric or oxide)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:24
L29	84	I19 and ((storage adj capacitor) near10 (material or conductive or conducting or metal or wiring))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:26
L30	42	I19 and ((storage adj capacitor) with (material or conductive or conducting or metal or wiring) with ((semiconductor or active) adj (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:27
L31	28	I19 and ((storage adj capacitor) with (material or conductive or conducting or metal or wiring) with gate with ((semiconductor or active) adj (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:27
L32	28	I19 and ((storage adj capacitor) with (material or conductive or conducting or metal or wiring) with gate with (insulating or dielectric) with ((semiconductor or active) adj (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:29
L33	23	I19 and ((storage adj capacitor) with (material or conductive or conducting or metal or wiring) with (gate adj (insulating or dielectric)) with ((semiconductor or active) adj (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:30
L34	14	I19 and ((storage adj capacitor) near10 (gate adj (insulating or dielectric)) near10 ((semiconductor or active) adj (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:31

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L35	16	l19 and ((capacitor) near10 (gate adj (insulating or dielectric)) near10 ((semiconductor or active) adj (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:31
L36	623	((capacitor) near10 (gate adj (insulating or dielectric)) near10 ((semiconductor or active) adj (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:32
L37	53	((capacitor) near10 (gate adj (insulating or dielectric)) near10 ((semiconductor or active) adj (layer or film))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:34
L38	26	((storage adj capacitor) near10 (gate adj (insulating or dielectric)) near10 ((semiconductor or active) adj (layer or film))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:34
L39	47	((storage adj capacitor) with (gate adj (insulating or dielectric)) with ((semiconductor or active) adj (layer or film))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:36
L40	41	((storage adj capacitor) with (gate adj (insulating or dielectric)) with ((semiconductor or active) adj (layer or film)) with (wiring or conductive or conducting or metal or electrode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:37
L41	25	((storage adj capacitor) with (gate adj (insulating or dielectric)) with ((semiconductor or active) adj (layer or film)) with (wiring or conductive or conducting or metal or electrode) with (gate adj electrode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:37
L42	210	((storage adj capacitor) with (gate adj (insulating or dielectric)) with ((semiconductor or active) adj (layer or film)) with (wiring or conductive or conducting or metal or electrode) with (gate adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:37



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L43	39	((storage adj capacitor) with (gate adj (insulating or dielectric)) with ((semiconductor or active) adj (layer or film)) with (wiring or conductive or conducting or metal or electrode) with (gate adj electrode) with channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:38
L44	301	((storage adj capacitor) same (gate adj (insulating or dielectric)) same ((semiconductor or active) adj (layer or film)) same (wiring or conductive or conducting or metal or electrode) same (gate adj electrode) with channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:39
L45	358	((storage adj capacitor) same (gate adj (insulating or dielectric)) same ((semiconductor or active) adj (layer or film)) same (wiring or conductive or conducting or metal or electrode) same (gate adj electrode) same channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:39
L46	140	((storage adj capacitor) same (gate adj (insulating or dielectric)) same ((semiconductor or active) adj (layer or film)) same (wiring or conductive or conducting or metal or electrode) same (gate adj electrode) same channel same (wire or wiring))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/01 13:39